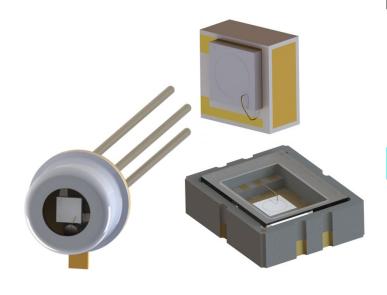


1.7μm cutoff wavelength

100μm - 1mm dia. active areas



APPLICATIONS

- Optical Power Measurement
- Spectroscopy
- Optical Testing
- Medical Diagnostics
- Fiber Optic receivers
- Free-Space Communication

AVAILABLE OPTIONS

- Through-Hole and Ceramic SMT Packaging
- Extended Wavelengths to 2.6 μm
- High Quantum Efficiency
- Custom Lenses, Filters, and Anti-Reflective Coatings
- Fiber-Optic Packaging
- Integrated Electronics:
 - Thermo-Electric Cooler
 - Transimpedance Amplifier

Specifications

Small Area InGaAs Photodiodes								
Part Number	N17S10-XX	N17S15-XX	N17S30-XX	N17S50-XX	N17S100-XX	Units		
Optoelectronic Characteristics @ 23 °C ± 2 °C								
Active Diameter	100	150	300	500	1000	μm		
Spectral Response Range	800-1700	800-1700	800-1700	800-1700	800-1700	nm		
Peak Wavelength (typ)	1550	1550	1550	1550	1550	nm		
Responsivity @ 850 nm (min/typ)	0.2/0.35	0.2/0.35	0.2/0.35	0.2/0.35	0.2/0.35	A/W		
Responsivity @ 1300 nm (min/typ)	0.85/1.0	0.85/1.0	0.85/1.0	0.85/1.0	0.85/1.0	A/W		
Responsivity @ 1550 nm (min/typ)	0.93/1.1	0.93/1.1	0.93/1.1	0.93/1.1	0.93/1.1	A/W		
R _{SHUNT} @ 10mV (min/typ)	1000/2000	1000/2000	200/550	180/250	50/180	МΩ		
I _{DARK} @ V _R (typ/max)	0.05/1 @ 5 V	0.1/1 @ 5 V	0.55 @ 5 V	0.8/5 @ 5 V	1/8 @ 5 V	nA		
Capacitance @ 0 V (max)	1.9	2.4	25	40	250	pF		
Capacitance @ V _R (max)	1.2 @ 5 V	1.8 @ 5 V	8 @ 5 V	18 @ 5 V	110 @ 5 V	pF		
NEP @ λ _{PEAK} @ 5 V (min)	4	6	12	16	22	fW/Hz ^{1/2}		
Linearity (±0.2 dB) @ 5V (min/typ)	6/8	6/8	6/8	6/8	6/8	dBm		
Storage Temperature	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	°C		
Operating Temperature	-40 to 85	-40 to 85	-40 to 85	-40 to 85	-40 to 85	°C		
Maximum Ratings @ 23 °C ± 2 °C								
Reverse Voltage	25	25	25	20	15	V		
Reverse Current	10	10	10	10	10	mA		
Forward Current	10	10	10	10	10	mA		



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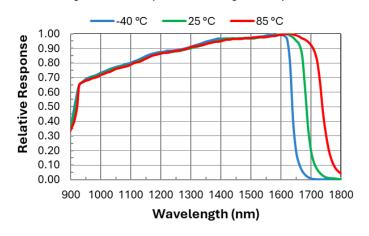
SENSING FURTHER

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1.7μm cutoff wavelength 100μm - 1mm dia. active areas

Figure 1. InGaAs Response vs. Wavelength vs. Temperature



-40 °C 25°C -85 °C 1.00 0.90 Relative Response 0.80 0.70 0.60 0.50 0.40 0.30 0.20 0.10 0.00 1500 1700 1550 1600 1650 1750 1800 Wavelength (nm)

Figure 2. InGaAs Response vs. Wavelength vs. Temperature (Cont.)

Figure 3. Dark Current vs. Reverse Voltage vs. Diameter

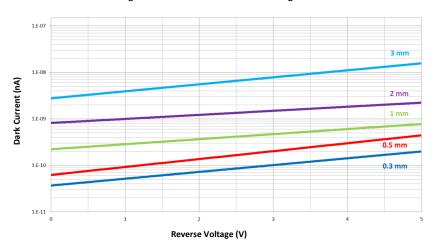
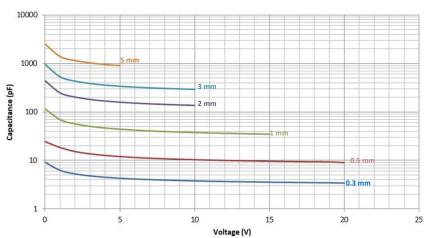


Figure 4. Capacitance (pF) vs. Reverse Voltage (V) vs. Diameter (mm)





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1.7μm cutoff wavelength 100μm - 1mm dia. active areas

Packaging Capabilities

Packaging Configurations							
Diameter (μm)	TO He	aders	Ceramic Leadless Chip Carrier				
	TO-46	TO-18	LCC-6				
100	•	•					
150	•	•					
300	•	•					
500	•	•	•				
1000	•	•	•				
Window (Other Options Available)							
Material	Molded Cl	ear Glass	Borosilicate Glass				
Thickness (mm)	0.2	25	0.5				

GPD QUALIFICATIONS

Our compliance, certificates, and capabilities

- ✓ ISO 9001:2015
- **✓ Quality Assurance Provisions**
- ✓ DDTC/ITAR registered
- ✓ MIL-STD-883
- ✓ MIL-STD-750

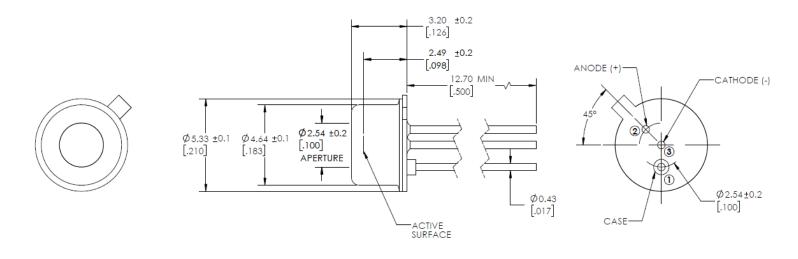
- ✓ Space-qualified designs
- High-reliability assembly and environmental/ radiation test
- ✓ Manufactured in Salem, NH



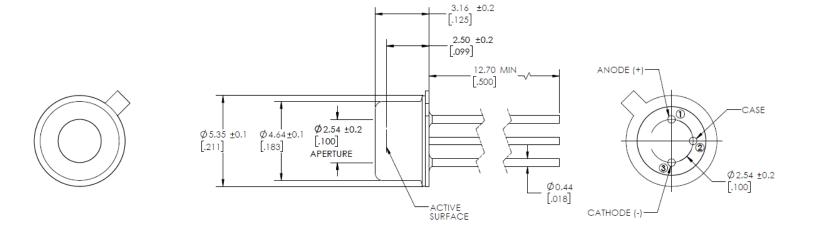
1.7μm cutoff wavelength 100μm - 1mm dia. active areas

Package Outlines

TO-46



TO-18



DIMENSIONS IN MM [INCH]



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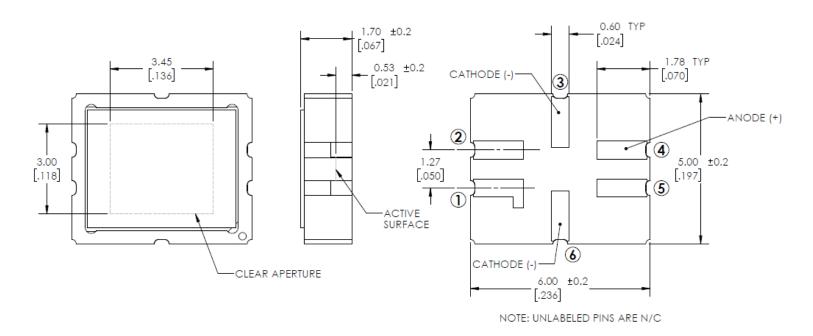
SENSING FURTHER



1.7μm cutoff wavelength 100μm - 1mm dia. active areas

Package Outlines

LCC-6



DIMENSIONS IN MM [INCH]



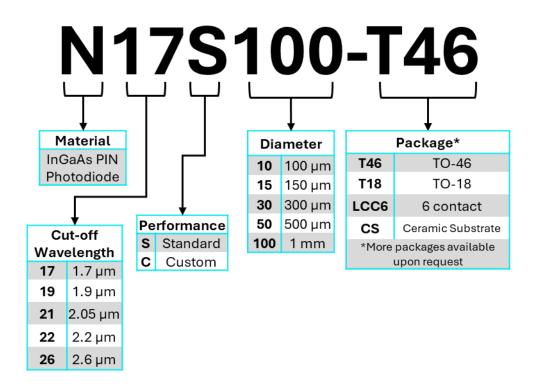


1.7μm cutoff wavelength 100μm - 1mm dia. active areas

Ordering Information

GPD is proud to offer multiple packaging solutions to best fit the needs of your application. Our Standard configurations are mentioned below, and custom packaging is also available.

Selection is based on the size of the photodiode and the package requirements of your application. Refer to packaging capabilities chart below for more information.



NOTE: GPD Optoelectronics may update product details without prior notice, and any use or application of our products is at your own discretion.





/ 1.7μm cutoff wavelength 100μm - 1mm dia. active areas

Handling and Processing Precautions

Electrostatic Discharge (ESD) Warning

Our detectors are highly susceptible to damage from electrostatic discharge (ESD). To prevent damage, use ESD protective measures, such as grounding straps, when unpacking and handling these devices.

To guarantee the optimal performance of a photodiode, it is crucial to adhere strictly to the device's electrical specifications. Photodiodes are highly sensitive to values that surpass their absolute maximum ratings. Exceeding these limits can lead to damage or total failure of the device. Users should employ handling techniques that avoid electrostatic discharges and other electrical surges during both the handling and operation of these devices.

Cleanroom Packaging and Handling

Our detectors are packaged in a clean state under cleanroom conditions, eliminating the need for cleaning before processing. In fact, cleaning is not recommended as it may introduce contaminants.

Processing Guidelines

To maintain the cleanliness of our detectors:

- Process under the cleanest conditions possible, including clean workplaces and room air.
- Wear suitable gloves or fingerstalls to prevent fingerprint contamination (mainly fats and organic acids).
- Ensure the soldering process is designed to prevent the need for post-soldering cleaning.

Cleaning Optical Windows (if necessary)

If exceptional circumstances require cleaning the optical windows:

- First, identify the type of contamination.
- For loose particles, gently blow them off with nitrogen gas or clean, dry air.
- For attached particles or other contaminating materials, clean with solvents such as isopropyl alcohol, or
 First Contact™ Polymer



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